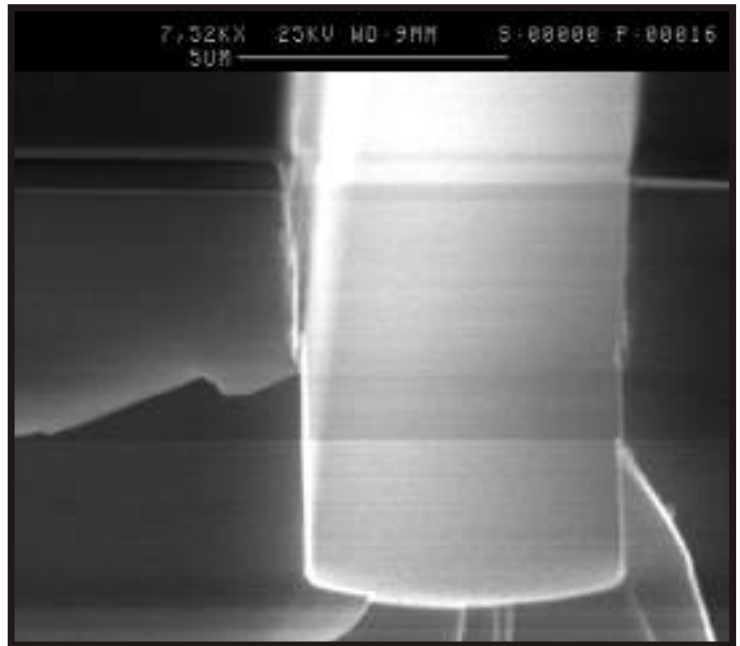
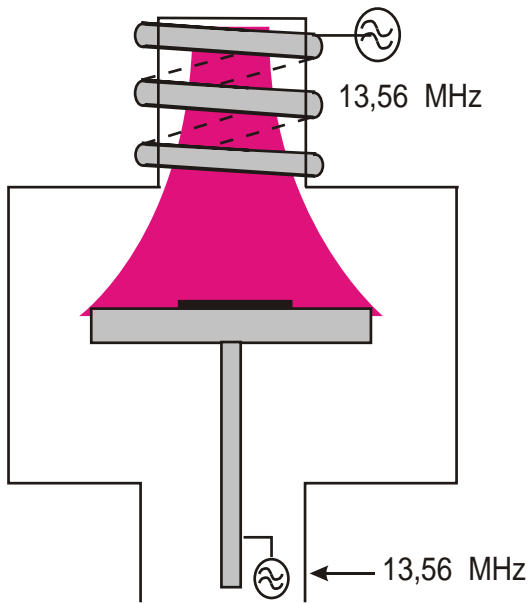


# Plasmalab Data

## GaSb ICP Etching



- Plasmalab 80 Plus*
- Plasmalab System 100*
- Plasmalab System 133*

OPT application lab:  
7 µm deep GaSb etch, Cl2 based

**Technology:**

Reactive Ion Etching  
with ICP Source (2 or 13 MHz)  
Inductive Coupled Plasma  
RF driven substrate electrode

**Results:**

Rate : 2 µm/ min  
selectivity to SiO2 mask 25 : 1  
good uniformity  
smooth surface  
anisotropic profile

